NSL12AWT1G

High Current Surface Mount PNP Silicon Low $V_{CE(sat)}$ Transistor for Battery Operated Applications

Features

- High Current Capability (3 A)
- High Power Handling (Up to 650 mW)
- Low $V_{CE(s)}$ (170 mV Typical @ 1 A)
- Small Size
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Benefits

- High Specific Current and Power Capability Reduces Required PCB Area
- Reduced Parasitic Losses Increases Battery Life

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	−12	Vdc
Collector-Base Voltage	V_{CBO}	−12	Vdc
Emitter-Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous − Peak	I_C I_{CM}	−2.0 −3.0	Adc
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

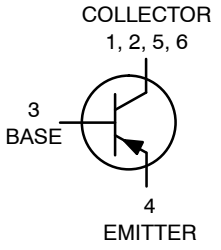
Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 1)	450 3.6	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$ (Note 1)	275	°C/W
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 2)	650 5.2	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$ (Note 2)	192	°C/W
Thermal Resistance, Junction−to−Lead 6	$R_{\theta JL}$	105	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P_D Single	1.4	W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. FR−4, Minimum Pad, 1 oz Coverage
2. FR−4, 1″ Pad, 1 oz Coverage

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http://onsemi.com

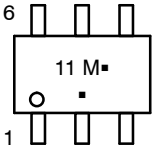
12 VOLTS
3.0 AMPS
PNP TRANSISTOR





SC−88/SOT−363
CASE 419B
STYLE 20

MARKING DIAGRAM



M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage, (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−12	−15	–	Vdc
Collector – Base Breakdown Voltage, (I_C = −0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	−12	−25	–	Vdc
Emitter – Base Breakdown Voltage, (I_E = −0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	−7.0	–	Vdc
Collector Cutoff Current, (V_{CB} = −12 Vdc, I_E = 0)	I_{CBO}	–	−0.02	−0.1	μAdc
Collector−Emitter Cutoff Current, (V_{CES} = −12 Vdc, I_E = 0)	I_{CES}	–	−0.03	−0.1	μAdc
Emitter Cutoff Current, (V_{CES} = −5.0 Vdc, I_E = 0)	I_{EBO}	–	−0.03	−0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (I_C = −0.5 A, V_{CE} = −1.5 V) (I_C = −0.8 A, V_{CE} = −1.5 V) (I_C = −1.0 A, V_{CE} = −1.5 V)	h_{FE}	 100 100 100	 180 165 160	 – 300 –	
Collector – Emitter Saturation Voltage (Note 3) (I_C = −0.5 A, I_B = −10 mA) (I_C = −0.8 A, I_B = −16 mA) (I_C = −1.0 A, I_B = −20 mA)	$V_{CE(sat)}$	 – – –	 −0.10 −0.14 −0.17	 −0.160 −0.235 −0.290	V
Base – Emitter Saturation Voltage (Note 3) (I_C = −1.0 A, I_B = −20 mA)	$V_{BE(sat)}$	–	−0.84	−0.95	V
Base – Emitter Turn−on Voltage (Note 3) (I_C = −1.0 A, V_{CE} = −1.5 V)	$V_{BE(on)}$	–	−0.81	−0.95	V
Cutoff Frequency (I_C = −100 mA, V_{CE} = −5.0 V, f = 100 MHz)	f_T	–	100	–	MHz
Output Capacitance (V_{CB} = −1.5 V, f = 1.0 MHz)	C_{obo}	–	50	65	pF

3. Pulsed Condition: Pulse Width < 300 μsec, Duty Cycle < 2%

ORDERING INFORMATION

Device	Package	Shipping†
NSL12AWT1G	SOT−363 (Pb−Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

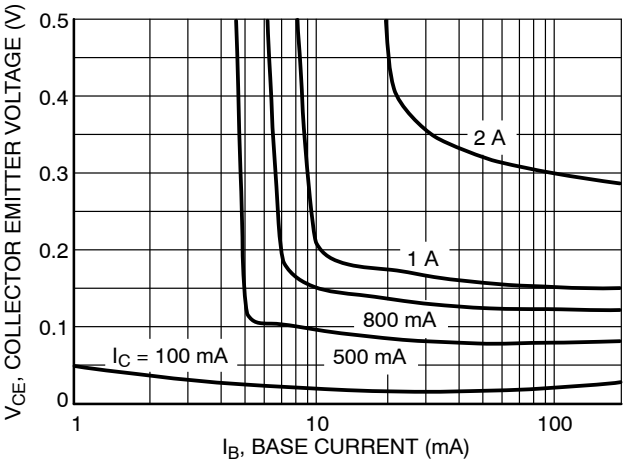


Figure 1. Collector Emitter Voltage vs Base Current

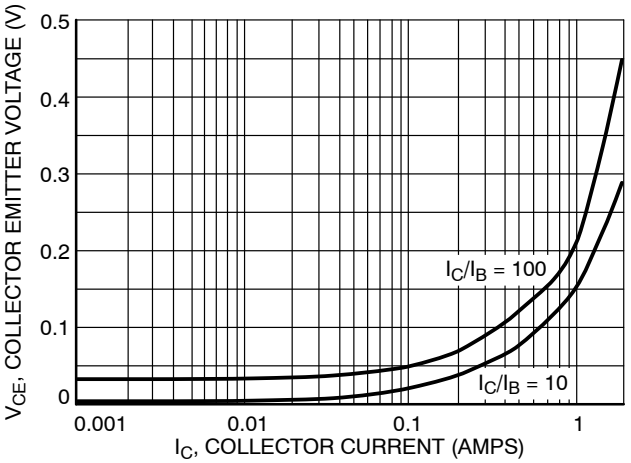


Figure 2. Collector Emitter Voltage vs Collector Current

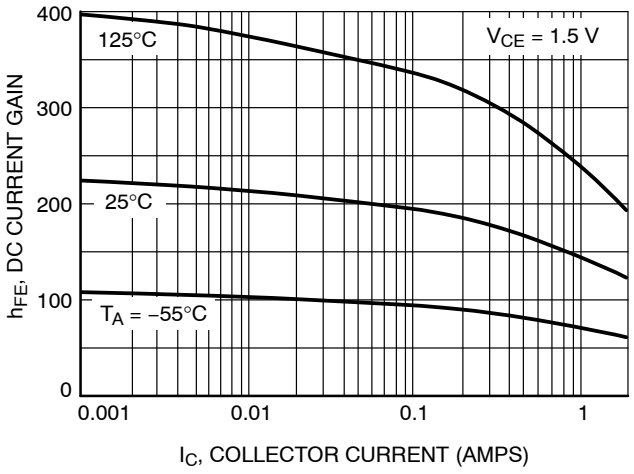


Figure 3. DC Current Gain versus Collector Current

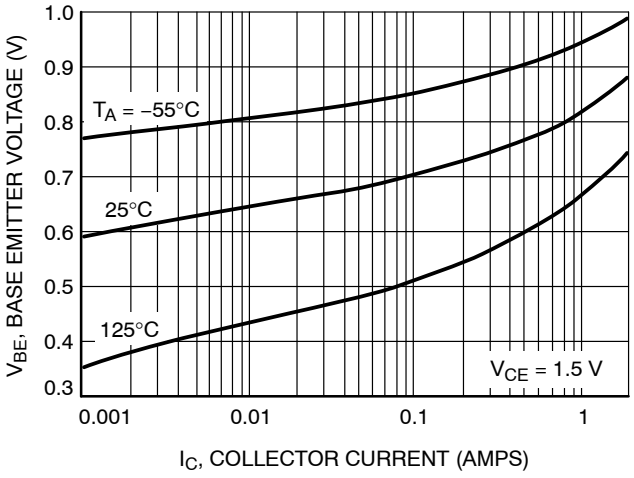


Figure 4. Base Emitter Voltage versus Collector Current

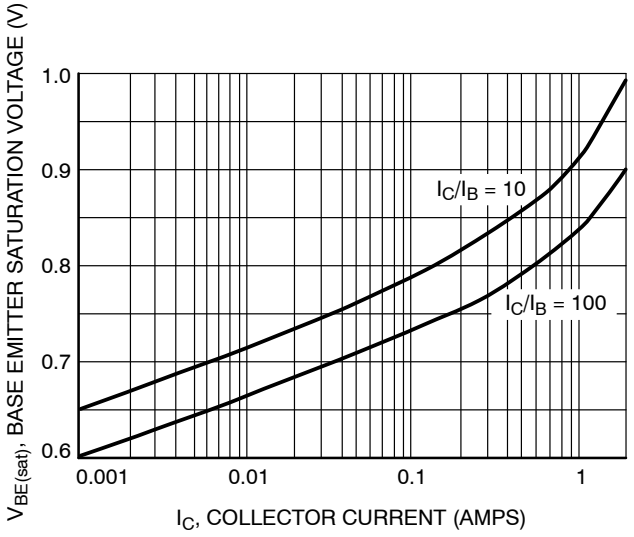


Figure 5. Base Emitter Saturation Voltage versus Base Current

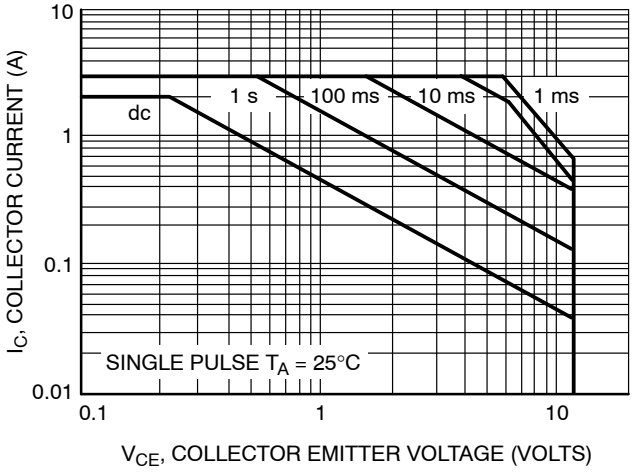


Figure 6. Safe Operating Area

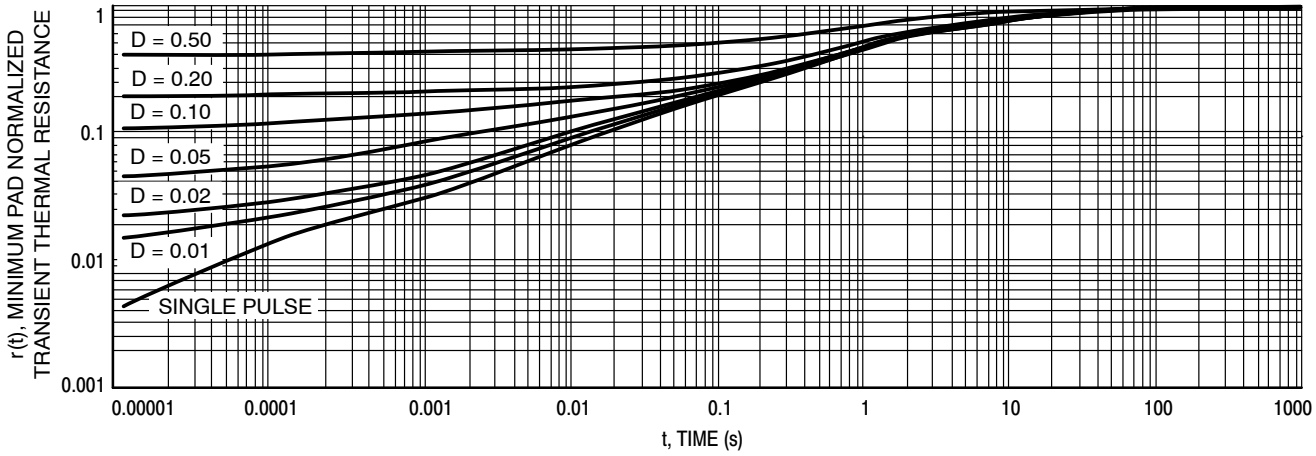
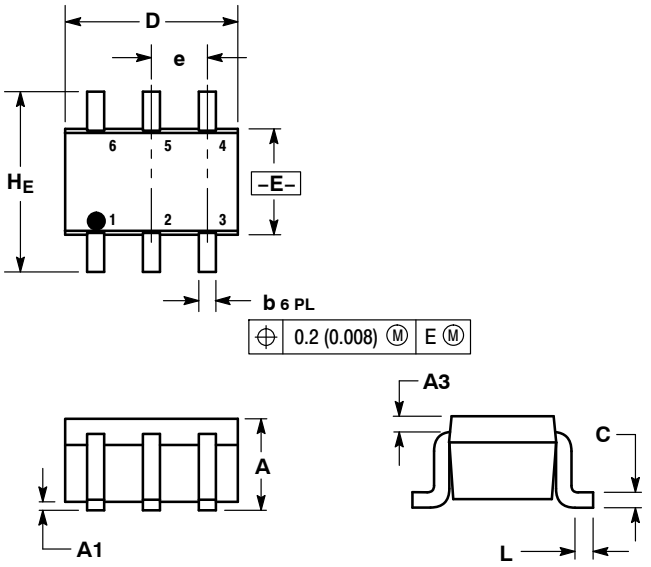


Figure 7. Normalized Thermal Response

PACKAGE DIMENSIONS

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE W

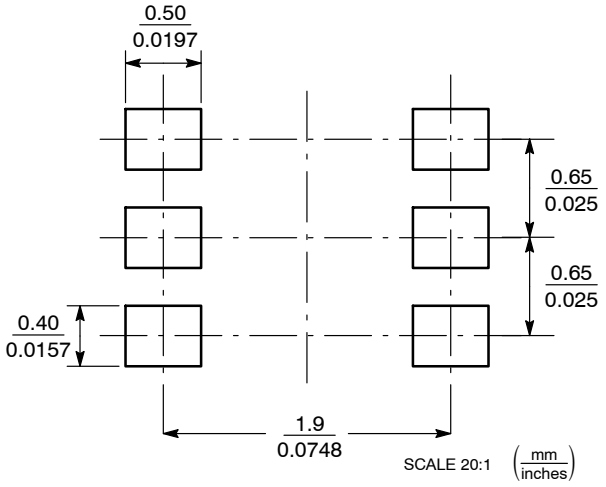


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B−01 OBSOLETE, NEW STANDARD 419B−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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